NL17SZ05

Product Preview

Single Inverter with Open Drain Outputs

The NL17SZ05 is a high performance single inverter with open drain outputs operating from a 1.65 to 5.5 V supply.

The Output stage is open drain with Over Voltage Tolerance. This allows the NL17SZ05 to be used to interface 5.0 V circuits to circuits of any voltage between 0 and +7.0 V.

Features

- Tiny SOT−953 Package
- Extremely High Speed: t_{PD} 2.5 ns (typical) at V_{CC} = 5.0 V
- Designed for 1.65 V to 5.5 V V_{CC} Operation, CMOS Compatible
- LVCMOS Compatible
- 24 mA Output Sink Capability, Pullup may be between 0 and 7.0 V
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 20
- These Devices are Pb−Free and are RoHS Compliant

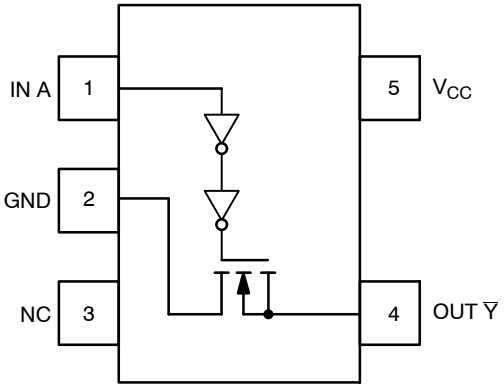

Figure 1. Pinout (Top View)

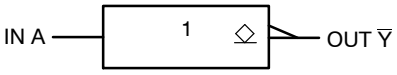

Figure 2. Logic Symbol

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

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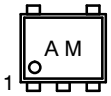
MARKING DIAGRAM

SOT−953
CASE 527AE



A = Specific Device Code
M = Month Code

PIN ASSIGNMENT

Pin	Function
1	IN A
2	GND
3	NC
4	OUT $\overline{Y}$
5	V_{CC}

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	Z
H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +7.0$	V
V_O	DC Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	-0.5 to V_{CC} + 0.5 −0.5 to + 0.5	V
I_{IK}	DC Input Diode Current	V_I < GND	−50	mA
I_{OK}	DC Output Diode Current	V_O < GND	−50	mA
I_O	DC Output Sink Current		±50	mA
I_{CC}	DC Supply Current Per Supply Pin		±100	mA
I_{GND}	DC Ground Current Per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
P_D	Power Dissipation in Still Air	SOT−353 SOT−553	186 135	mW
θ_{JA}	Thermal Resistance	SOT−353 SOT−553	350 496	°C/W
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
ESD	ESD Classification	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	Class IC Class A N/A	
$I_{Latch-Up}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 3)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22−A115−A, rated to EIA/JESD22−A115−A.
2. Tested to JESD22−C101−A.
3. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage	(Z or LOW State)	0	V_{CC}	V
T_A	Operating Free−Air Temperature		−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ±0.2 V V_{CC} = 3.0 V ±0.3 V V_{CC} = 5.0 V ±0.5 V	0 0 0	20 10 5	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V_{CC} 0.7 V_{CC}			0.75 V_{CC} 0.7 V_{CC}		V
V_{IL}	Low−Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.25 V_{CC} 0.3 V_{CC}		0.25 V_{CC} 0.3 V_{CC}	V
I_{LKG}	Z−State Output Leakage Current	V_{IN} = V_{IL} V_{OUT} = V_{CC} or GND	2.3 to 5.5			±5.0		±10.0	μA
V_{OL}	Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
		I_{OL} = 4 mA	1.65		0.08	0.24		0.24	
		I_{OL} = 8 mA	2.3		0.22	0.3		0.3	
		I_{OL} = 12 mA	2.7		0.22	0.4		0.4	
		I_{OL} = 16 mA	3.0		0.28	0.4		0.4	
		I_{OL} = 24 mA	3.0		0.38	0.55		0.55	
		I_{OL} = 32 mA	4.5		0.42	0.55		0.55	
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I_{OFF}	Power Off Leakage Current	V_{IN} = 5.5 V or V_{OUT} = 5.5 V	0			1.0		10	μA
I_{CC}	Quiescent Supply Current	V_{IN} = 5.5 V or GND	5.5			1.0		10	μA

AC ELECTRICAL CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

Symbol	Parameter	Condition	V_{CC} (V)	T_A = 25°C			−55°C ≤ T_A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PZL}	Propagation Delay (Figure 3 and 4)	$R_{L\,=}$ R_1= 500 Ω, C_L = 50 pF	1.65	0.8	5.3	11.6	0.8	12.0	ns
			2.5 ± 0.2	0.8	3.0	3.6	0.8	4.1	
			3.3 ± 0.3	0.8	2.4	3.2	0.8	3.7	
			5.0 ± 0.5	0.5	2.4	3.0	0.5	3.5	
t_{PLZ}	Propagation Delay (Figure 3 and 4)	$R_{L\,=}$ R_1= 500 Ω, C_L = 50 pF	1.65	0.8	5.3	11.6	0.8	12.0	ns
			2.5 ± 0.2	0.8	2.5	3.6	0.8	4.1	
			3.3 ± 0.3	0.8	2.1	3.2	0.8	3.7	
			5.0 ± 0.5	0.5	1.2	3.0	0.5	3.5	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	> 2.5	pF
C_{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	4.0	pF
C_{PD}	Power Dissipation Capacitance (Note 4)	10 MHz, V_{CC} = 5.5 V, V_I = 0 V or V_{CC}	4.0	pF

4. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no−load dynamic power consumption; P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

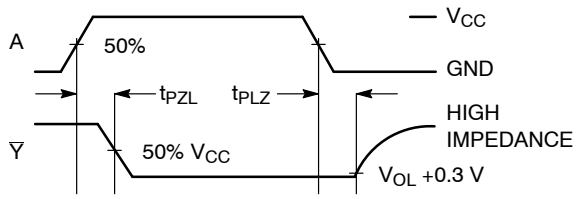
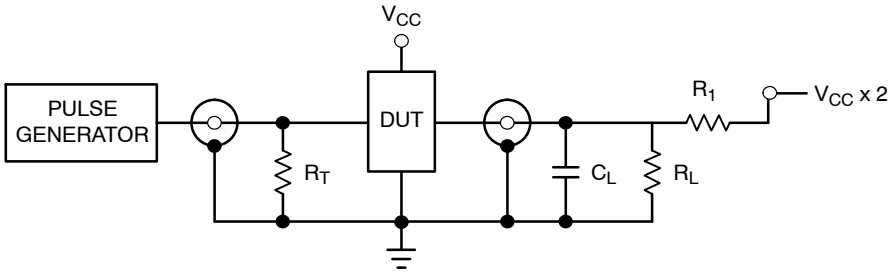


Figure 3. Switching Waveforms



R_T = Z_{OUT} of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

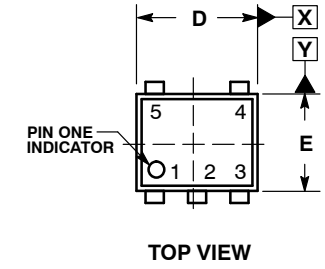
DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping†
NL17SZ05P5T5G	SOT−953 (Pb−Free)	8000 / Tape & Reel

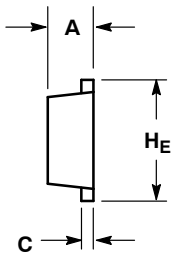
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

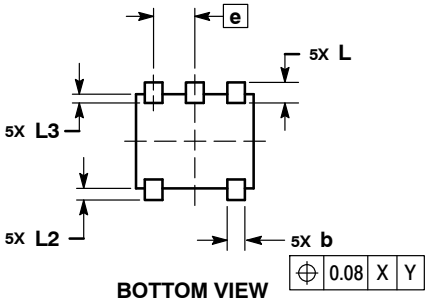
SOT−953
CASE 527AE
ISSUE E



TOP VIEW



SIDE VIEW

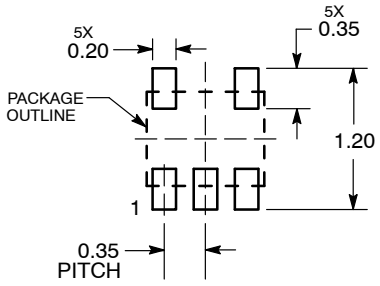


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H_E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	−−−	−−−	0.15

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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